

IN THE SPECIFICATION

Please replace the paragraph on page 5 lines 25-31, corresponding to paragraph [0020], with the following amended paragraph:

A method of manufacturing a thin film transistor array panel is provided, which includes: forming a gate wire and a storage electrode wire; depositing a gate insulating layer, an amorphous silicon layer, a contact layer, and a metal conductive layer; patterning the metal amorphous silicon layer, the contact layer, and the metal conductive layer to form a data wire, a direction control electrode, and a channel portion of a thin film transistor; forming a passivation layer on the channel portion; and forming a pixel electrode and a connecting portion on the passivation layer.

LAW OFFICES OF
MACPHERSON KWOK CHEN &
HED LLP
2402 MICHELSON DRIVE
SUITE 210
IRVINE, CA 92613
(949) 752-7040
FAX (408) 352-9203